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(54) **LID ASSEMBLY APPARATUS AND METHODS FOR SUBSTRATE PROCESSING CHAMBERS**

(71) Applicant: **Applied Materials, Inc.**, Santa Clara, CA (US)

(72) Inventors: **Hanish Kumar PANAVALAPPIL KUMARANKUTTY**, Bangalore (IN); **Prashant A. DESAI**, Bangalore (IN); **Diwakar N. KEDLAYA**, San Jose, CA (US); **Sumit AGARWAL**, Dublin, CA (US); **Vidyadharan Srinivasa Murthy BANGALORE**, Bengaluru (IN); **Truong NGUYEN**, Milpitas, CA (US); **Zubin HUANG**, Santa Clara, CA (US)

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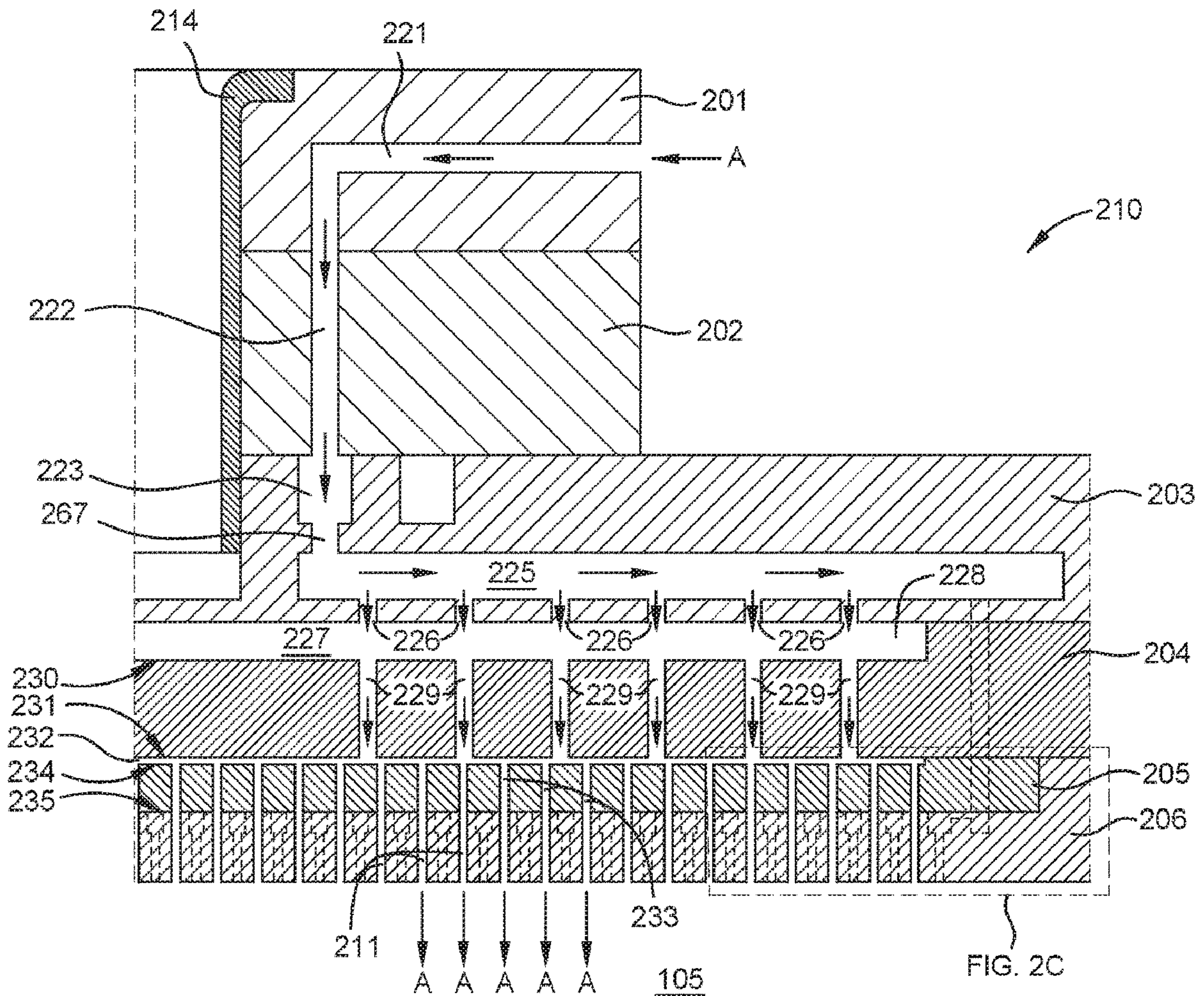
(57) **ABSTRACT**

The present disclosure relates to a lid assembly apparatus and related methods for substrate processing chambers. In one implementation, a lid assembly includes a gas manifold. The gas manifold includes a first gas channel configured to receive a process gas, a second gas channel configured to receive a doping gas, and a third gas channel configured to receive a cleaning gas. The lid assembly also includes a showerhead. The showerhead includes one or more first gas openings that are configured to receive the process gas, and one or more second gas openings that are configured to receive the doping gas.



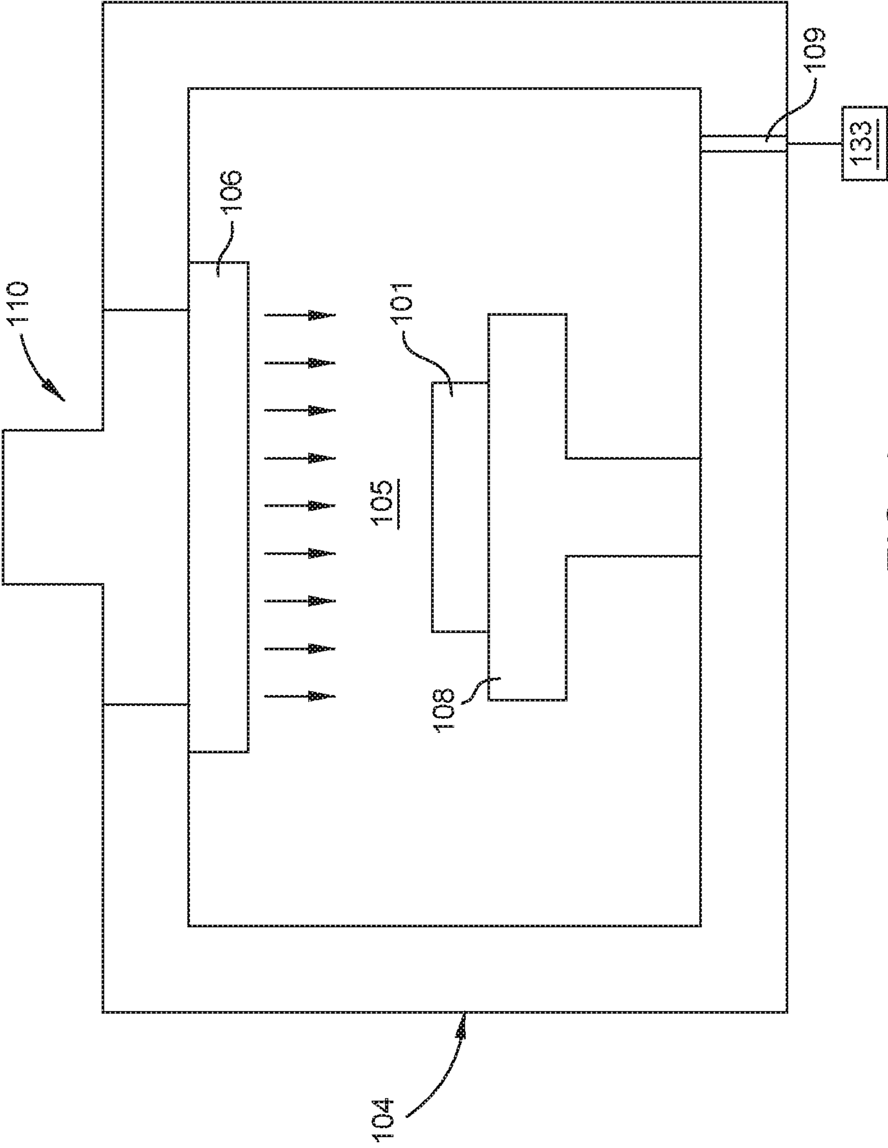


FIG. 1

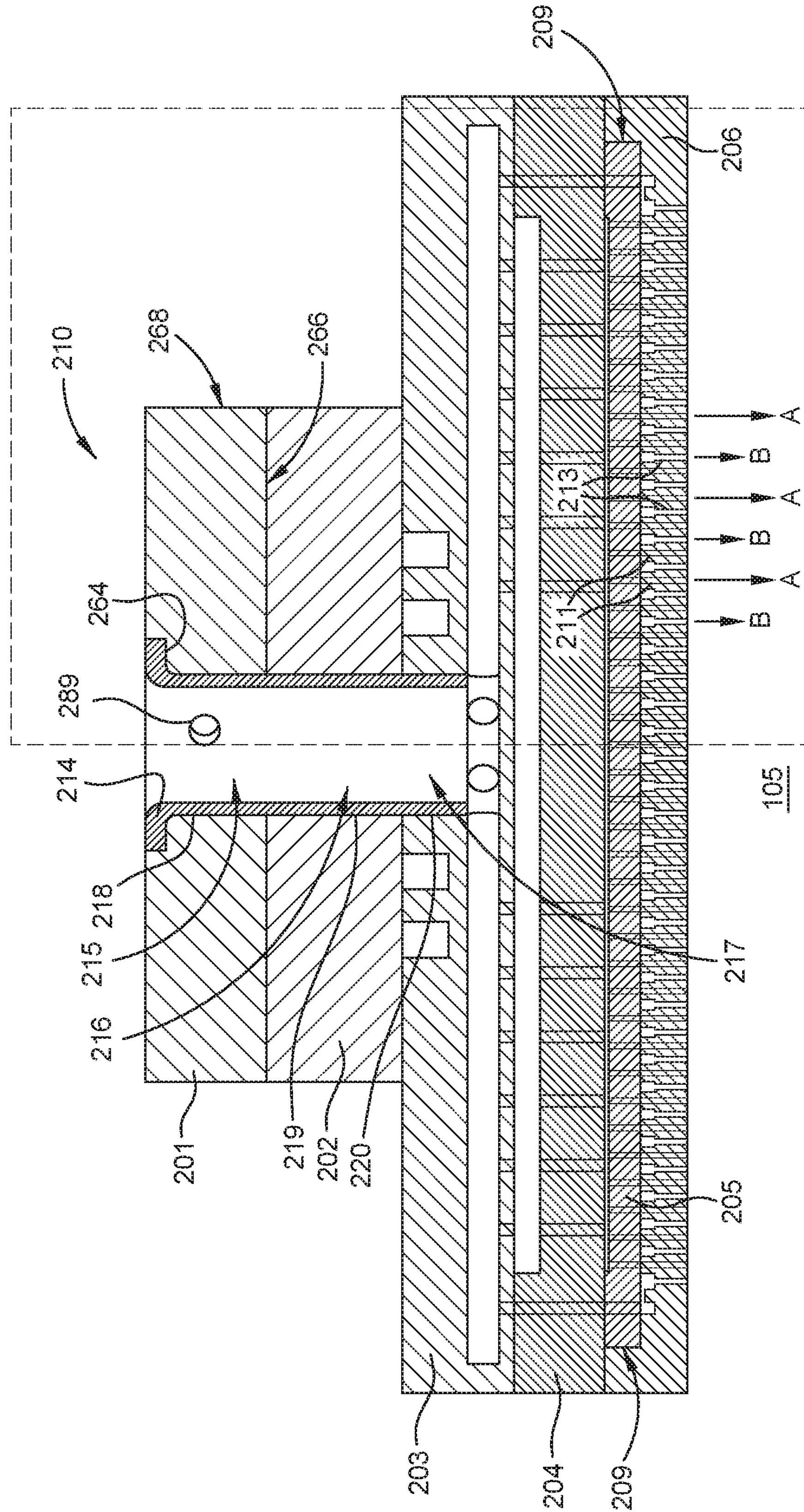


FIG. 2A

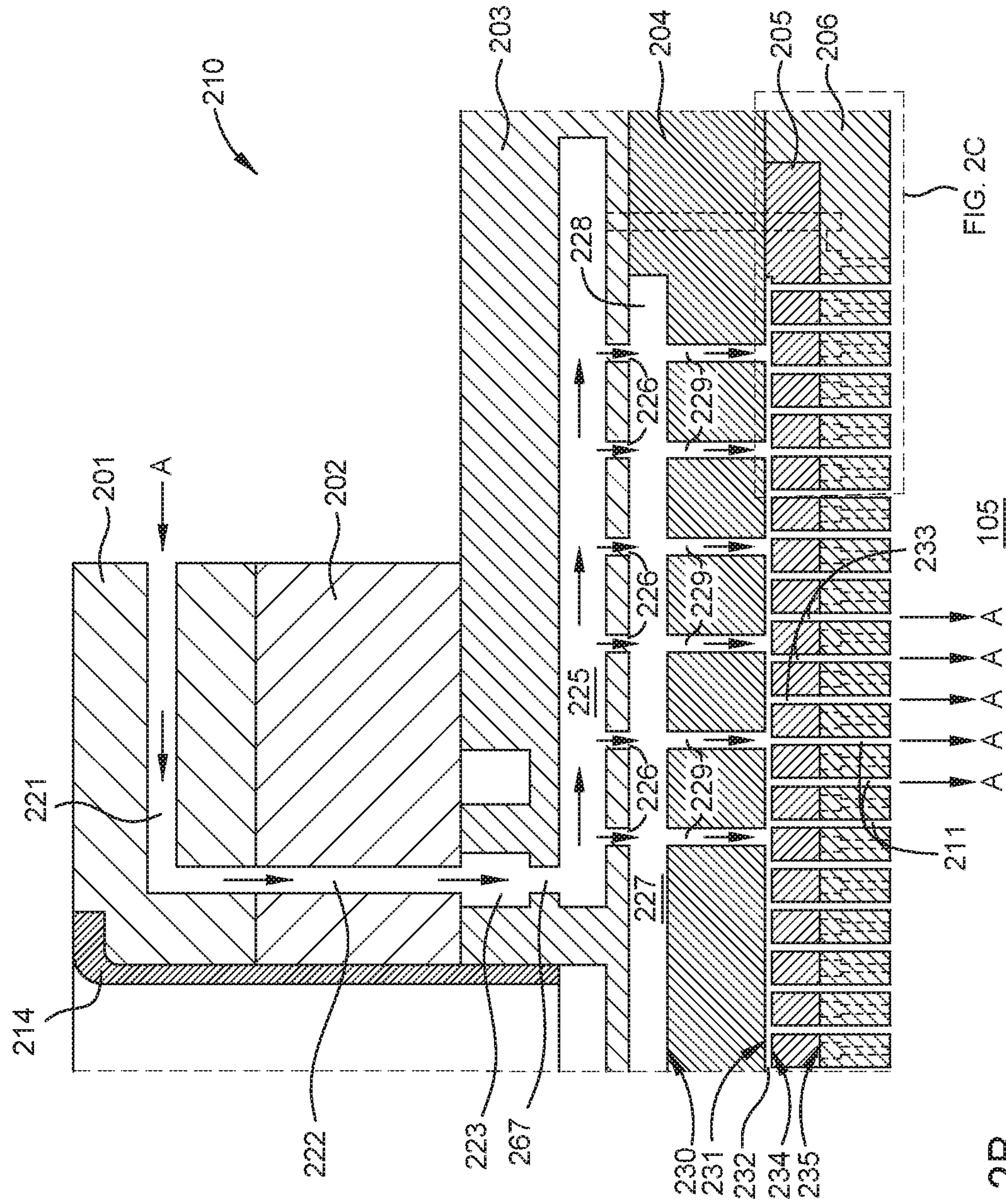


FIG. 2B

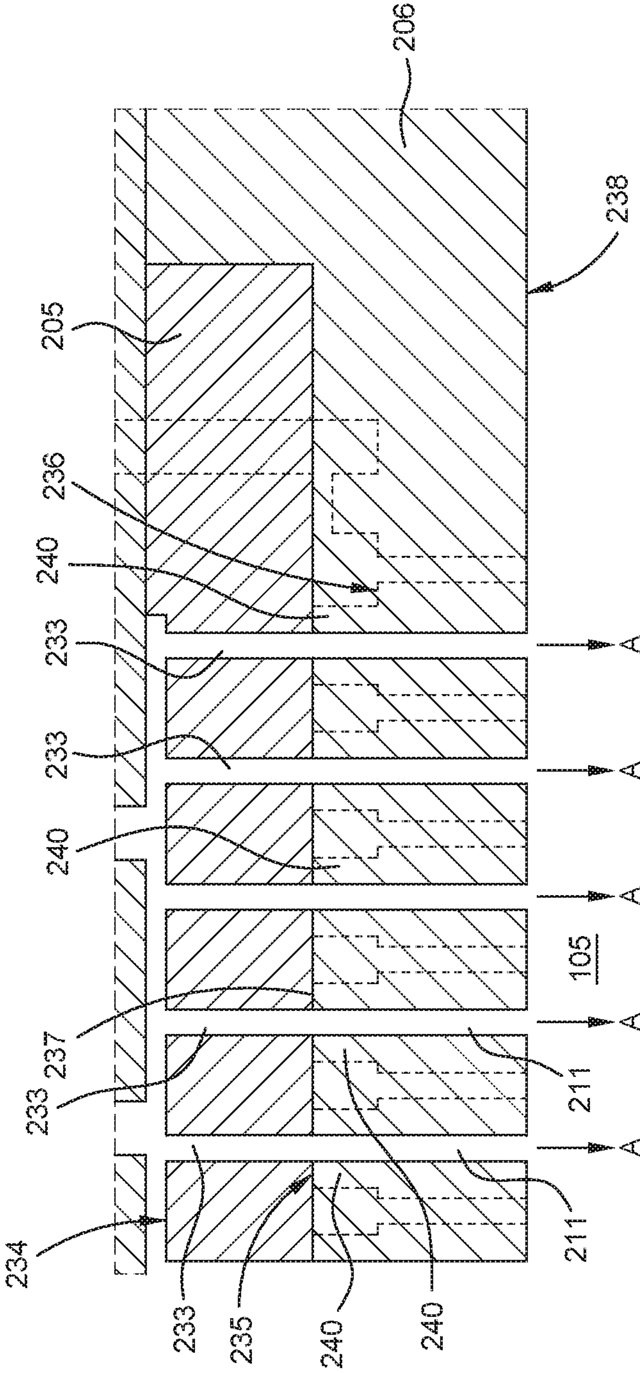


FIG. 2C

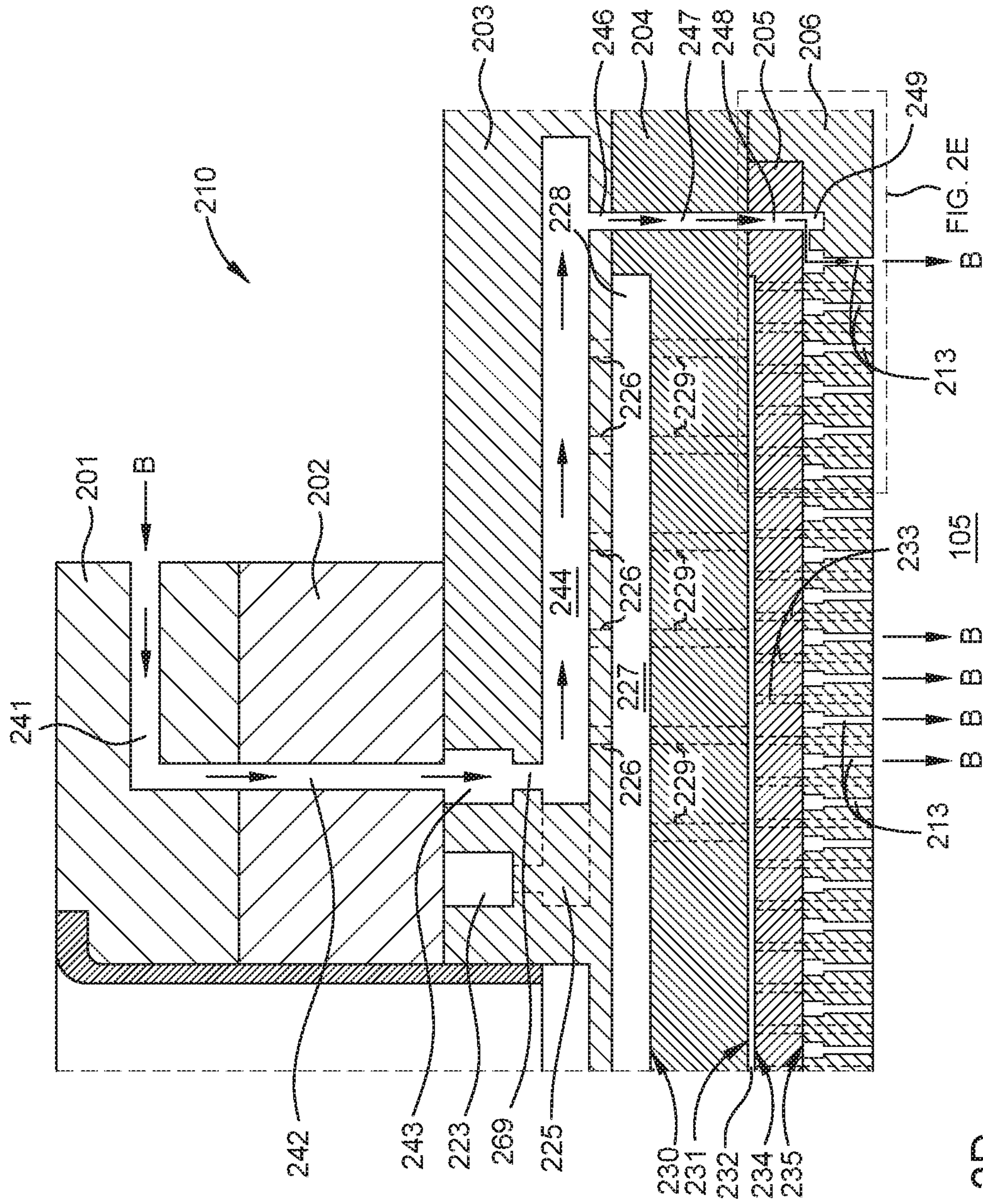


FIG. 2D

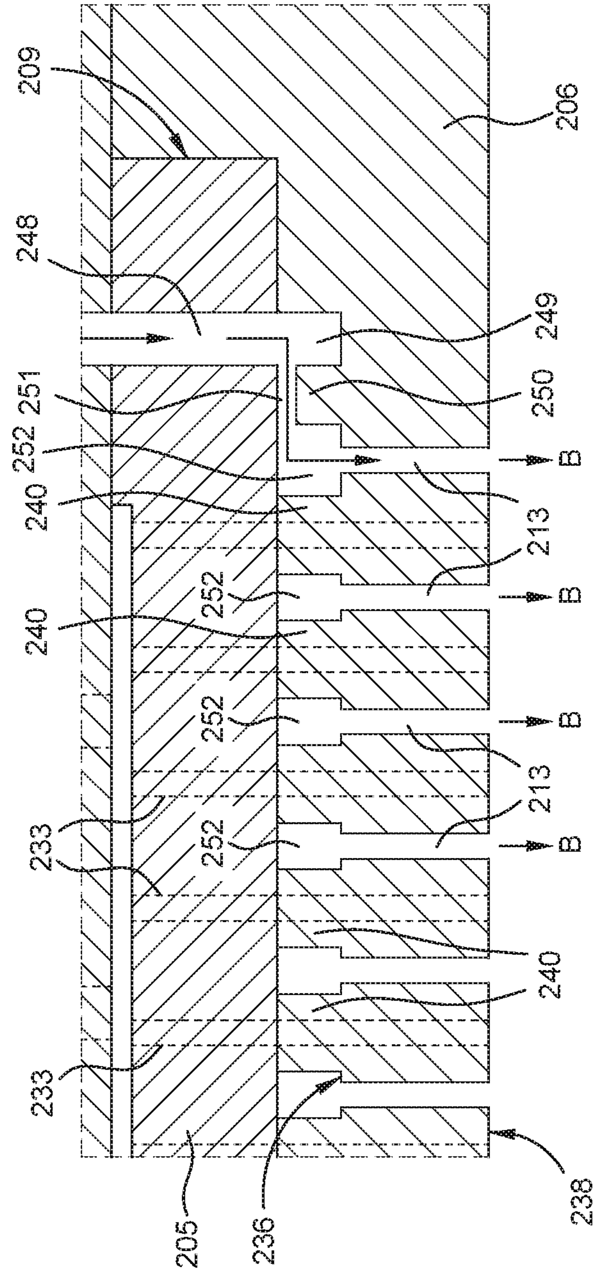


FIG. 2E

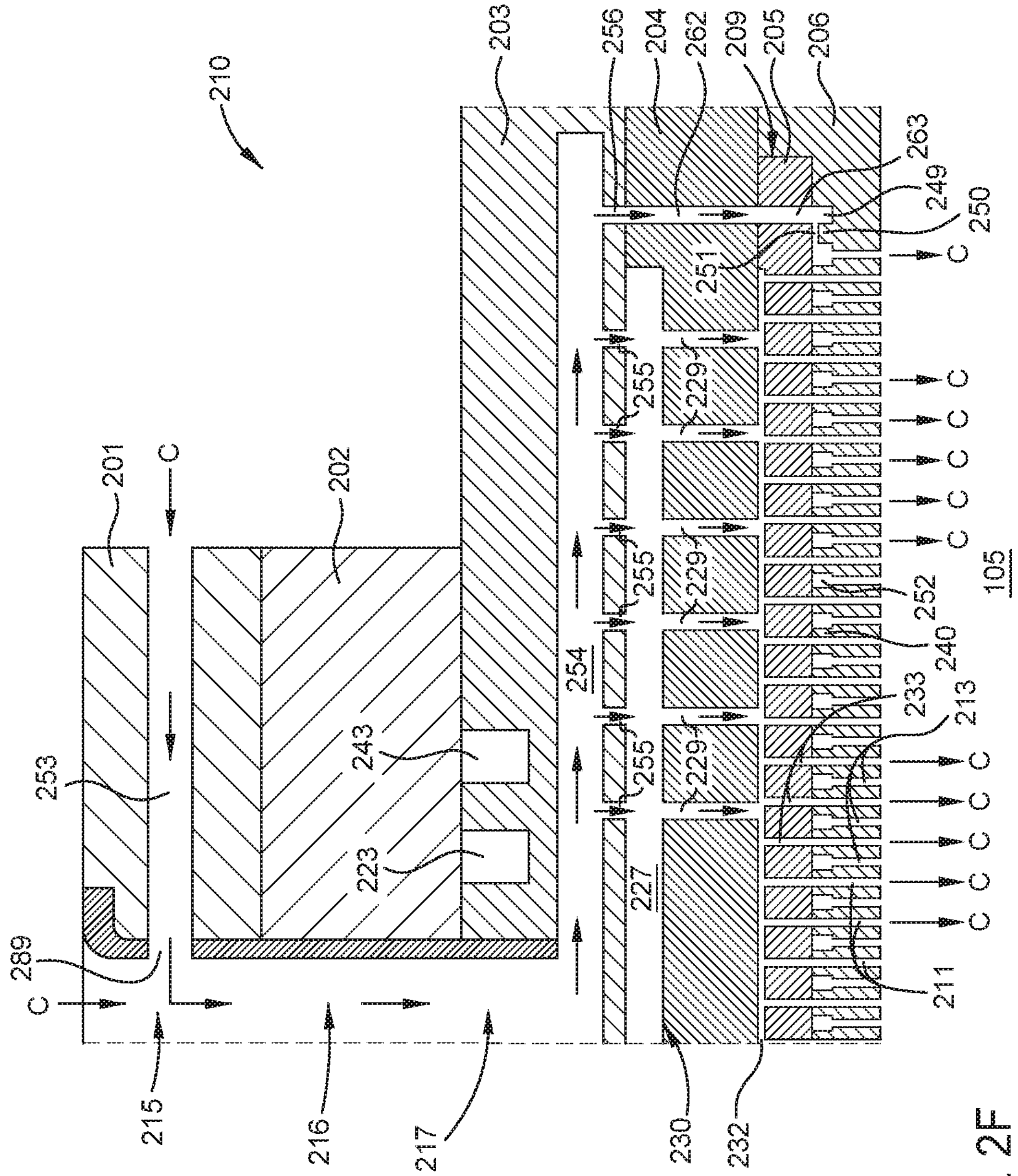


FIG. 2F

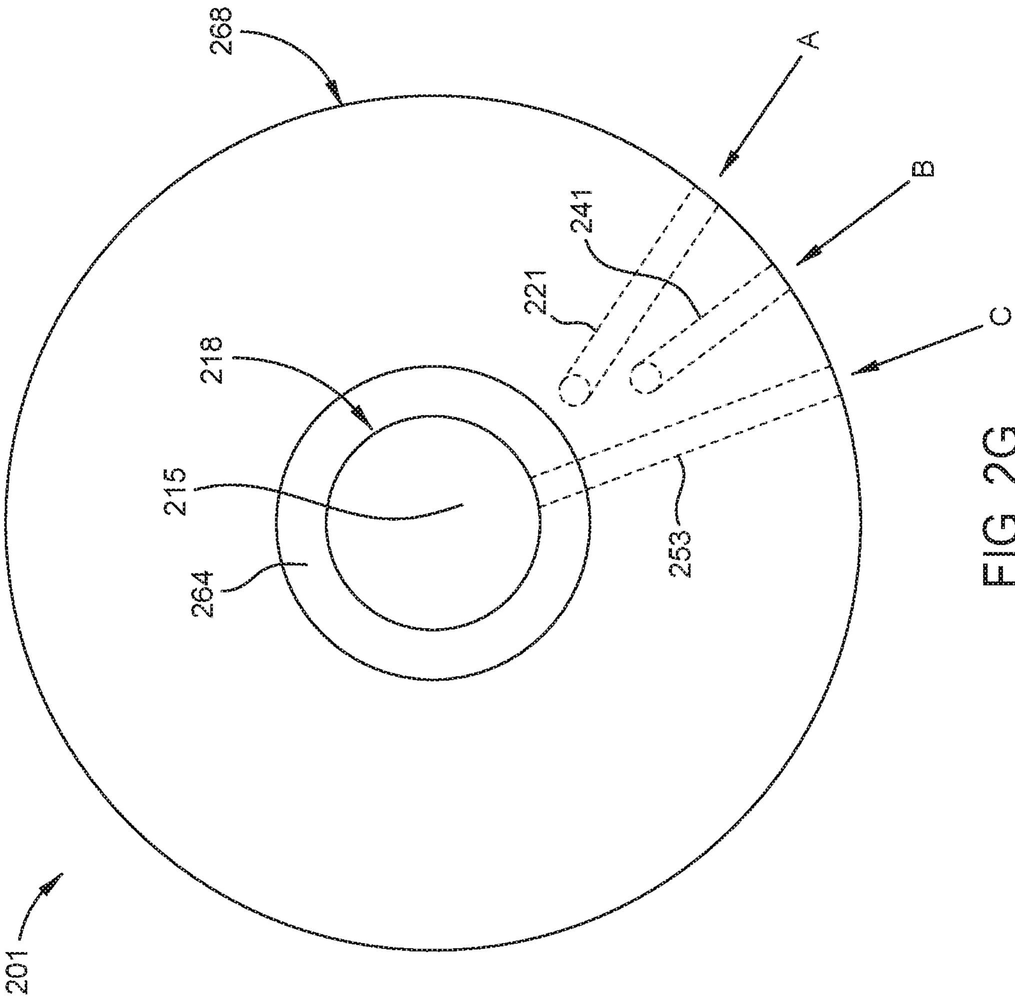


FIG. 2G

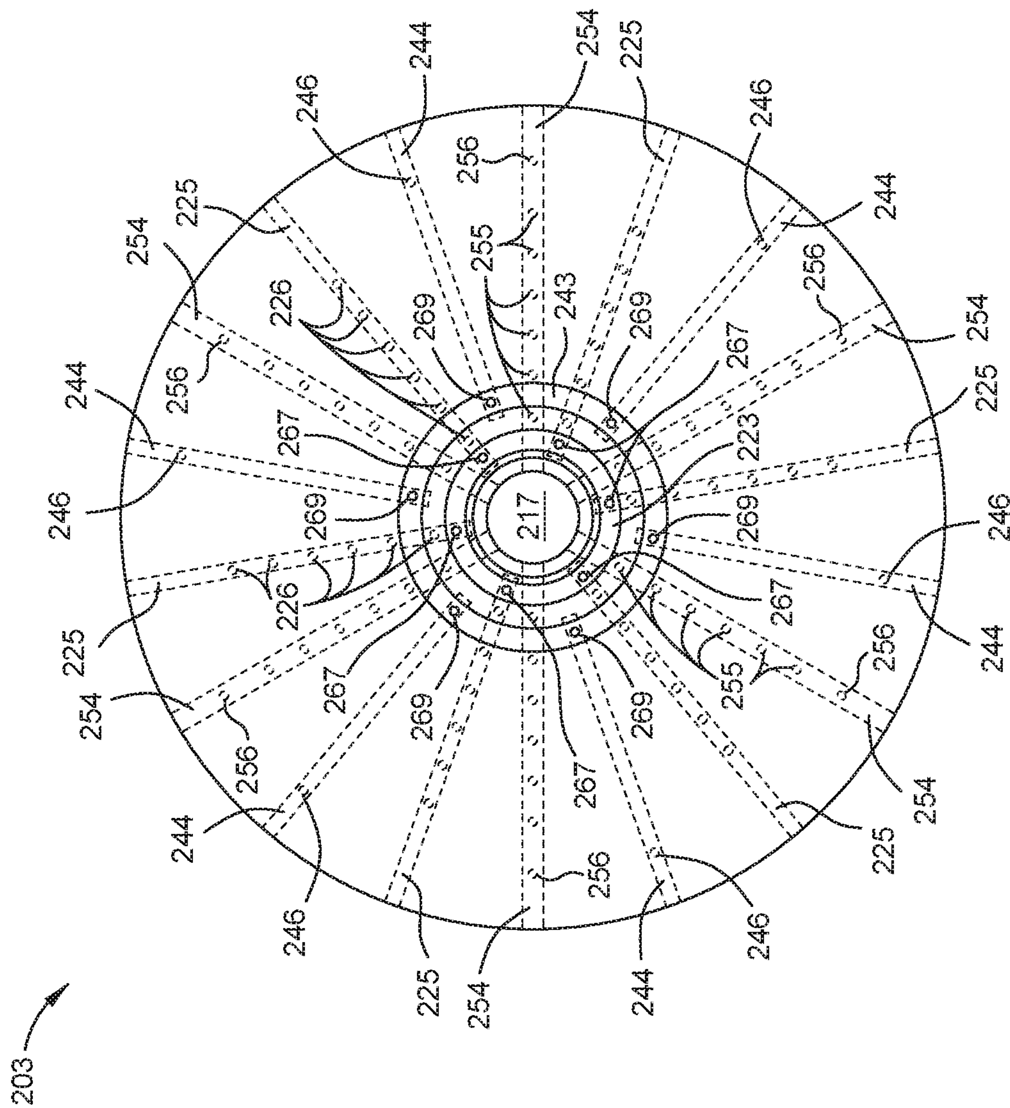


FIG. 2H

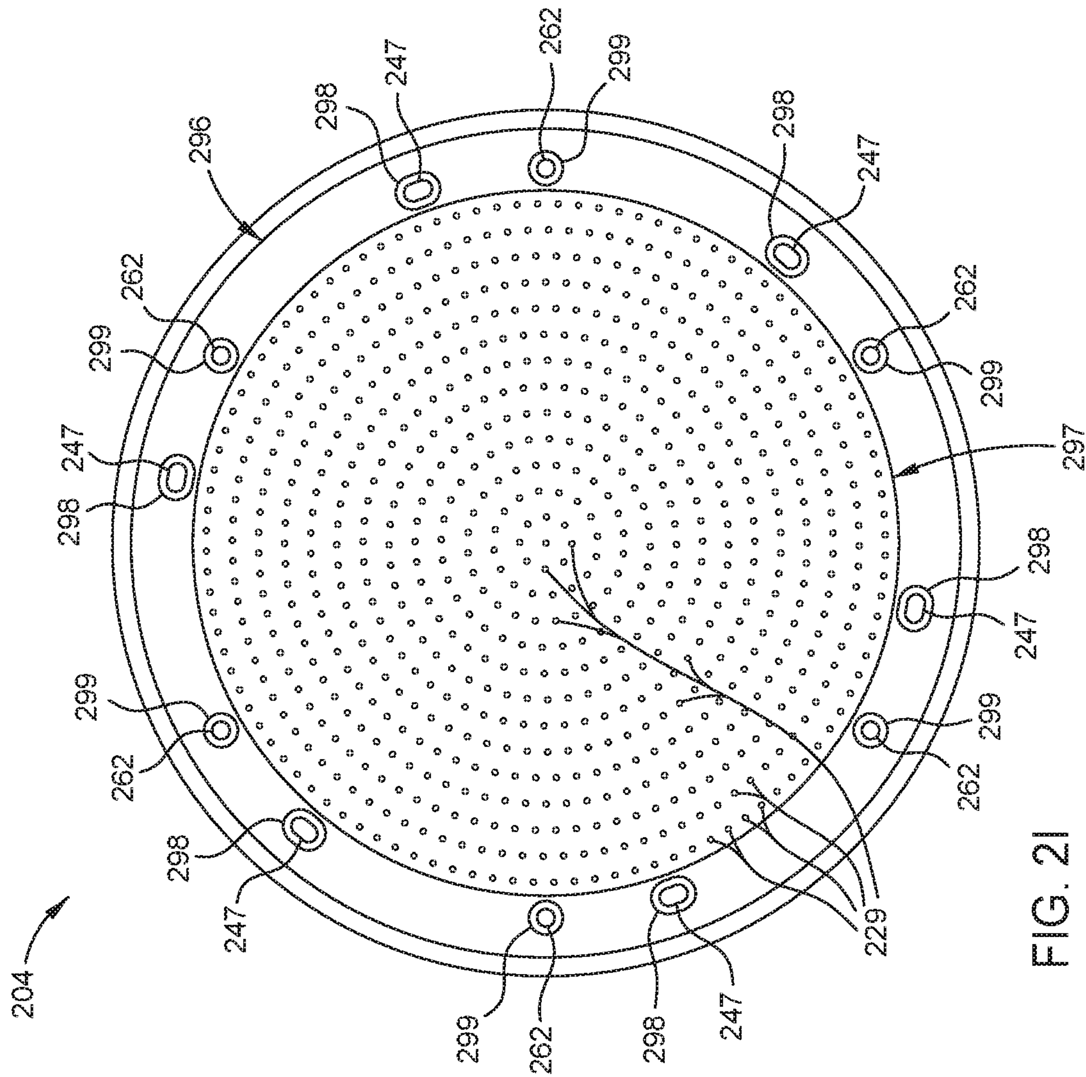


FIG. 2I

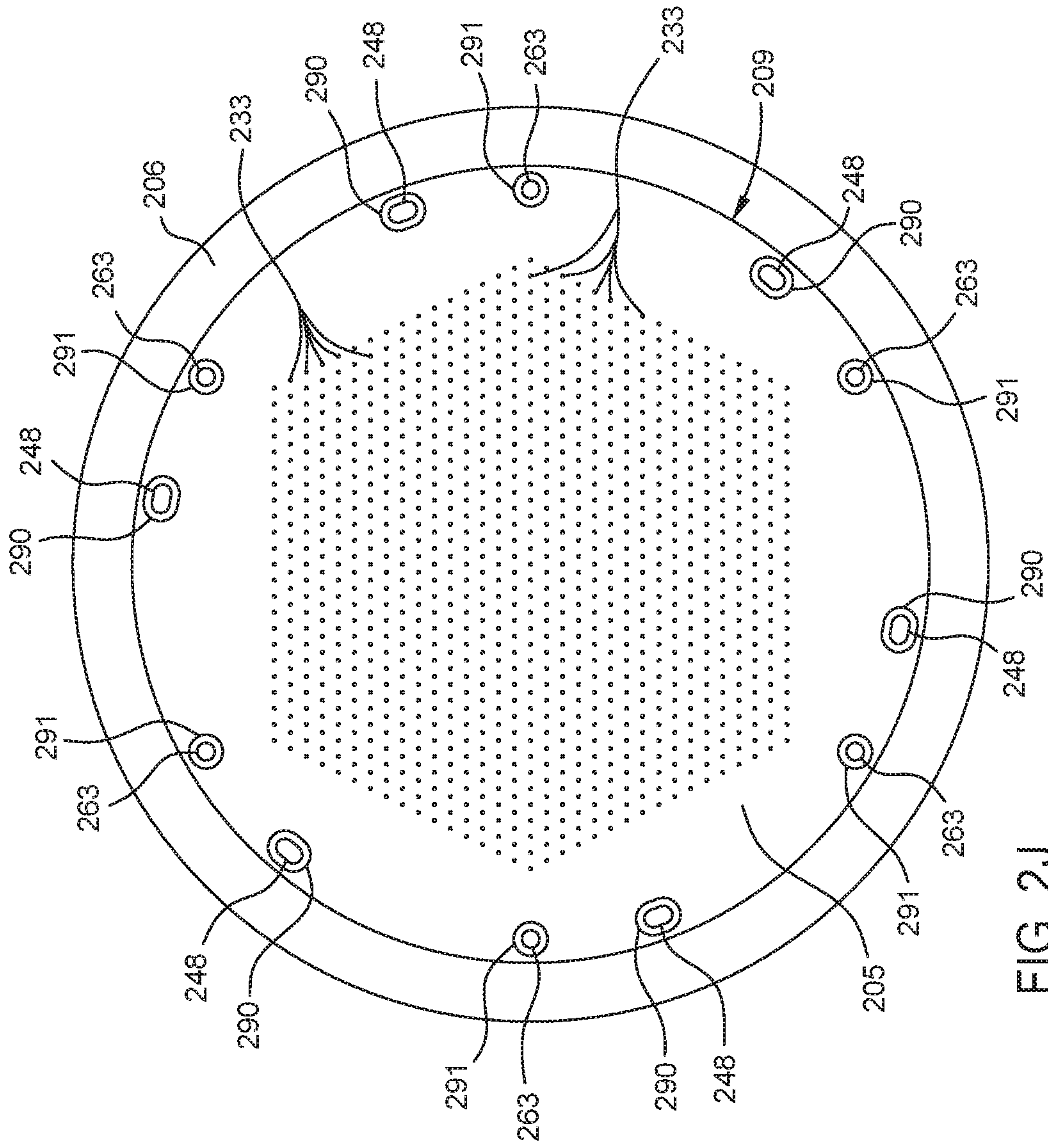


FIG. 2J

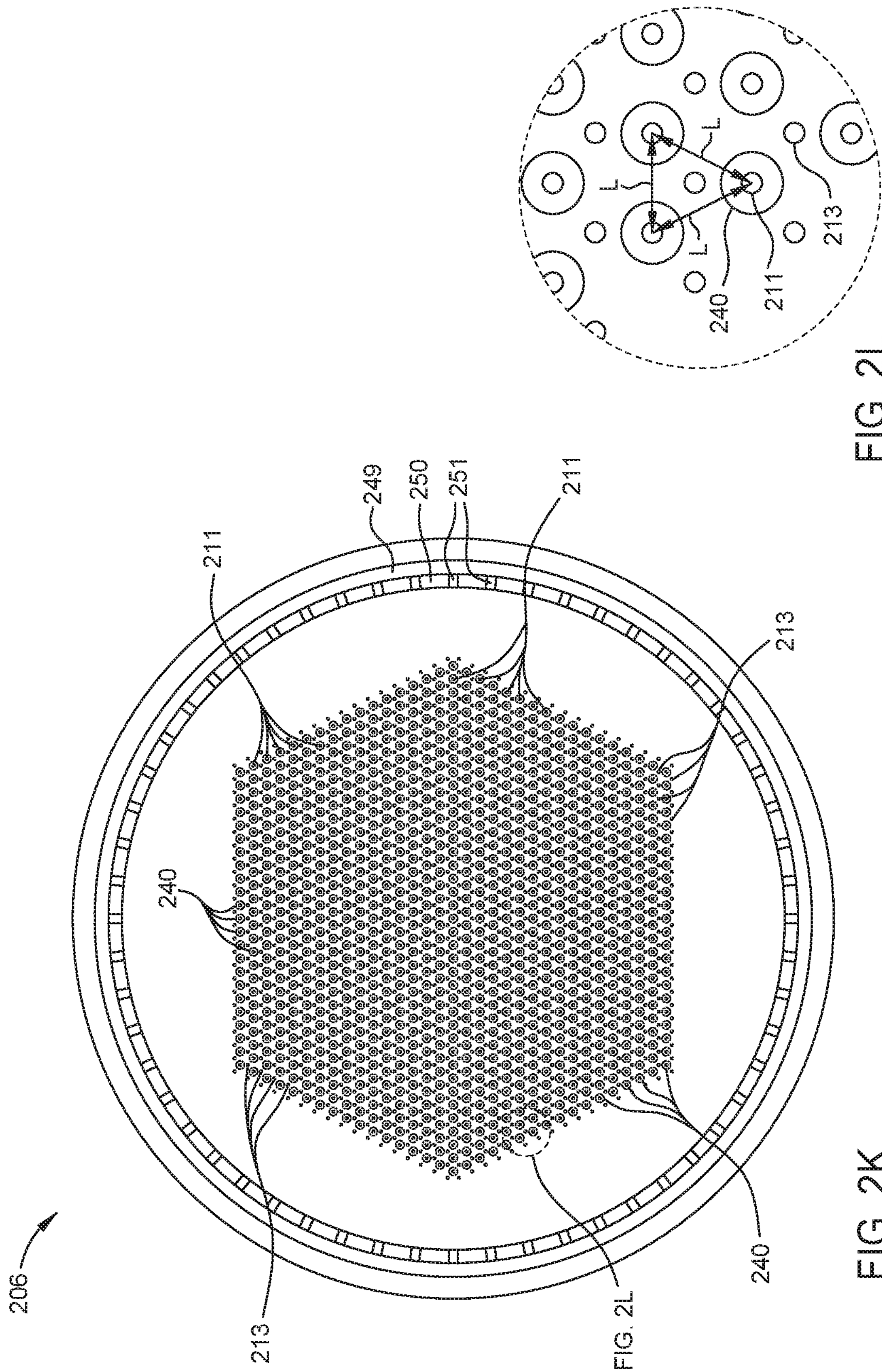


FIG. 2K

FIG. 2L

LID ASSEMBLY APPARATUS AND METHODS FOR SUBSTRATE PROCESSING CHAMBERS

BACKGROUND

Field

[0001] The present disclosure generally relates to a lid assembly apparatus and related methods for substrate processing chambers.

Description of the Related Art

[0002] Reactive gases are often used in the production of semiconductor devices. Some reactive gases, upon introduction to a chamber, will deposit a material upon substrates or sections of substrates. Certain gases break down easier and/or more quickly than other gases. For example some gases might break down easier and/or more quickly than other gases at certain temperatures. This results in inefficiency, waste, contamination, and reliability issues for substrate processing operations. For example, gases breaking down can cause reliability issues for a high-k dielectric that was deposited onto a semiconductor during substrate processing operations.

[0003] Therefore there is a need for an apparatus that delivers gases to the substrate processing chamber efficiently and reliably.

SUMMARY

[0004] The present disclosure relates to a lid assembly apparatus and related methods for substrate processing chambers.

[0005] In one implementation, a lid assembly includes a gas manifold. The gas manifold includes a first gas channel configured to receive a process gas, a second gas channel configured to receive a doping gas, and a third gas channel configured to receive a cleaning gas. The lid assembly also includes a showerhead. The showerhead includes one or more first gas openings that are configured to receive the process gas, and one or more second gas openings that are configured to receive the doping gas.

BRIEF DESCRIPTION OF THE DRAWINGS

[0006] So that the manner in which the above recited features of the present disclosure can be understood in detail, a more particular description of the disclosure, briefly summarized above, may be had by reference to embodiments, some of which are illustrated in the appended drawings. It is to be noted, however, that the appended drawings illustrate only exemplary implementations and are therefore not to be considered limiting of its scope, and may admit to other equally effective implementations.

[0007] FIG. **1** is a schematic illustration of a substrate processing chamber, according to one implementation of the present disclosure.

[0008] FIG. **2**A is a schematic illustration of a lid assembly, according to one implementation of the present disclosure.

[0009] FIG. **2**B is an enlarged partial illustration of the lid assembly illustrated in FIG. **2**A, according to one implementation of the present disclosure.

[0010] FIG. **2**C is an enlarged partial illustration of the showerhead illustrated in FIG. **2**B, according to one implementation of the present disclosure.

[0011] FIG. **2**D is an enlarged partial illustration of the lid assembly illustrated in FIG. **2**A, according to one implementation of the present disclosure.

[0012] FIG. **2**E is an enlarged partial illustration of the showerhead illustrated in FIG. **2**D, according to one implementation of the present disclosure.

[0013] FIG. **2**F is an enlarged partial illustration of the lid assembly illustrated in FIG. **2**A, according to one implementation of the present disclosure.

[0014] FIG. **2**G is a schematic top-view illustration of the gas manifold illustrated in FIG. **2**A, according to one implementation of the present disclosure.

[0015] FIG. **2**H is a schematic top-view illustration of the gas box illustrated in FIG. **2**A, according to one implementation of the present disclosure.

[0016] FIG. **2**I is a schematic top-view illustration of the first plate illustrated in FIG. **2**A, according to one implementation of the present disclosure.

[0017] FIG. **2**J is a schematic top-view illustration of the second plate and the showerhead illustrated in FIG. **2**A, according to one implementation of the present disclosure.

[0018] FIG. **2**K is a schematic top-view illustration of the showerhead illustrated in FIG. **2**A, according to one implementation of the present disclosure.

[0019] FIG. **2**L is a partially-enlarged view of the showerhead illustrated in FIG. **2**K.

[0020] To facilitate understanding, identical reference numerals have been used, where possible, to designate identical elements that are common to the figures. It is contemplated that elements and features of one embodiment may be beneficially incorporated in other embodiments without further recitation.

DETAILED DESCRIPTION

[0021] The present disclosure relates to a lid assembly apparatus and related methods for substrate processing chambers. FIG. **1** is a schematic illustration of a substrate processing chamber **104**, according to one implementation of the present disclosure. The substrate processing chamber **104** includes a pedestal **108** for supporting substrates **101** thereon.

[0022] The substrate processing chamber **104** includes a lid assembly **110**. The lid assembly **110** is configured to introduce precursor gases and cleaning gases into a processing volume **105** of the substrate processing chamber **104**. The lid assembly **110** includes a showerhead **106** that introduces gases into the processing volume **105**. The precursor gases introduced into the processing volume **105** are configured to react on or above the substrate **101** for the purposes of depositing a material onto the substrate **101**. The material deposited onto the substrate **101** may include a high-k dielectric material for the purposes of producing a semiconductor. Plasma is created in the processing volume **105** to facilitate deposition of the material onto the substrate **101**. The substrate processing chamber **104** includes one or more energy sources that propagate radio frequency (RF) energy, direct current (DC) voltage, and/or alternating current (AC) throughout the substrate processing chamber **104** and/or components thereof. The substrate processing chamber **104** includes one or more heaters and/or one or more cooling channels, such as in the pedestal **108**, that control the

temperatures of various components and aspects of the substrate processing chamber **104**.

[0023] The substrate processing chamber **104** includes an exhaust opening **109**. The exhaust opening **109** is fluidly connected to a vacuum pump **133**. The vacuum pump **133** is configured to exhaust gases from the processing volume **105** of the substrate processing chamber **104** through the exhaust opening **109**.

[0024] FIG. **2**A is a schematic illustration of a lid assembly **210**, according to one implementation of the present disclosure. One or more features, components, and/or aspects of the lid assembly **210** may be included in the lid assembly **110** and/or the showerhead **106** illustrated in FIG. **1**.

[0025] The lid assembly **210** includes a gas manifold **201**, an isolator manifold **202**, a gas box **203**, a first plate **204**, a showerhead **206**, and a second plate **205**. The gas manifold **201** is configured to receive two or more precursor gases from two or more precursor gas sources, and is configured to receive one or more cleaning gases from one or more cleaning gas sources. The isolator manifold **202** is disposed under the gas manifold **201**. The isolator manifold **202** is configured to electrically isolate components or aspects above the isolator manifold **202**, such as the gas manifold **201**, from components or aspects below the isolator manifold **202**. For example, the isolator manifold is configured to electrically isolate the gas manifold **201** from one or more of RF energy, DC voltage, and/or AC current propagating throughout the processing volume **105**. The gas box **203** is disposed under the gas manifold **201** and the isolator manifold **202**. The first plate **204** is disposed under the gas box **203**. In one example, the first plate **204** is a blocker plate. The showerhead **206** is disposed under the first plate **204**. A second plate **205** is disposed between the showerhead **206** and the first plate **204**. The second plate **205** is disposed within an inner shoulder **209** of the showerhead **206**.

[0026] The showerhead **206** includes one or more first gas openings **211** and one or more second gas openings **213**. The first gas openings **211** are configured to introduce a first gas A into a processing volume **105** (illustrated in FIG. **1**). The second gas openings **213** are configured to introduce a second gas B into the processing volume **105**. The first gas A enters the lid assembly **210** through the gas manifold **201** and exits the lid assembly **210** through the first gas openings **211** of the showerhead **206**. The second gas B enters the lid assembly **210** through the gas manifold **201** and exits the lid assembly **210** through the second gas openings **213** of the showerhead **206**.

[0027] As an example, the first gas A includes a process gas. The process gas includes one or more of silane and/or disilane. The second gas B includes a doping gas. The doping gas includes one or more of boron, phosphine, fluorine, arsenic, and/or nitrogen trifluoride. However, other gases are also contemplated.

[0028] The lid assembly **210** and the showerhead **206** are configured such that the first gas A and the second gas B are separated until the first gas A exits the showerhead **206** through the first gas openings **211** and the second gas B exits the showerhead **206** through the second gas openings **213**. The first gas A and the second gas B do not mix until the first gas A and the second gas B reach the processing volume **105**. These configurations allow the respective densities of the first gas A and the second gas B to be relatively high, resulting in reliable mixing of the first gas A and the second gas B in the processing volume **105** and adjacent to a substrate being processed (such as substrate **101**).

[0029] These configurations also prevent or mitigate the effects of one of first gas A and second gas B completely or partially breaking down before or faster than the other of first gas A and second gas B. In an example where first gas A includes a process gas and second gas B includes a doping gas, the doping gas may break down earlier or faster than the process gas at a certain temperature. These configurations prevent or mitigate the effects of the doping gas breaking down relative to the process gas by keeping the process gas and doping gas separate until the process gas and the doping gas exit the showerhead **206** of the lid assembly **210**. By separating the first gas A and the second gas B, reactions between first gas A and second gas B can be prevented until first gas A and second gas B reach the processing volume **105**. As an example, reactions between first gas A and second gas B can be prevented until right above the surface of a substrate (such as the surface of substrate **101** that faces the showerhead **106** illustrated in FIG. **1**). This achieves increased efficiency, less waste, and reliable deposition of films onto substrates.

[0030] The lid assembly **210** includes an insulator **214**. The insulator **214** is disposed in a central opening **215** of the gas manifold **201**, a central opening **216** of the isolator manifold **202**, and a central opening **217** of the gas box **203**. The insulator **214** includes a ceramic shield. In one example, the insulator **214** includes aluminum nitride. The insulator **214** reduces or prevents heat buildup and/or radical buildup on an inner surface **218** of the gas manifold **201**, an inner surface **219** of the isolator manifold **202**, and an inner surface **220** of the gas box **203**. The insulator **214** includes an opening **289** that corresponds to the third gas channel **253** illustrated in FIG. **2**F.

[0031] FIG. **2**B is an enlarged partial illustration of the lid assembly **210** illustrated in FIG. **2**A, according to one implementation of the present disclosure. The gas manifold **201** is configured to receive the first gas A through a first gas channel **221** of the gas manifold **201**. The first gas channel **221** is fluidly connected to a first gas channel **222** of the isolator manifold **202**. The isolator manifold **202** is configured to receive the first gas A through the first gas channel **222**. The first gas channel **222** is fluidly connected to a first gas opening **223** of the gas box **203**. The gas box **203** is configured to receive the first gas A through the first gas opening **223**. The first gas opening **223** of the gas box **203** is fluidly connected to a first gas channel **225** of the gas box **203**.

[0032] The first gas channel **225** includes one or more first gas openings **226** (six are shown) that are configured to deliver the first gas A from the first gas channel **225** and into a plenum **227** of the first plate **204**. The plenum **227** is defined by a recess **228** of the first plate **204** and the gas box **203**. The recess **228** defines a first surface **230** of the first plate **204**. The first plate also includes a second surface **231**. The first plate **204** includes one or more first gas openings **229** that extend from the first surface **230** to the second surface **231** of the first plate **204**. The first gas openings **229** are fluidly connected to a plenum **232** that is between the second surface **231** of the first plate **204** and the second plate **205**. The first gas openings **229** are configured to deliver first gas A from the plenum **227** and into the plenum **232** between the first plate **204** and the second plate **205**.

[0033] The second plate **205** includes one or more first gas openings **233** that extend from a first surface **234** of the second plate **205** to a second surface **235** of the second plate **205**. In one example, one or more of the first gas openings **229** of the first plate **204** is aligned with one or more of the first gas openings **226** of the first gas channel **225** of the gas box **203**. In one example, one or more of the first gas openings **229** of the first plate **204** is aligned with one or more of the first gas openings **233** of the second plate **205**.

[0034] The first gas openings **233** of the second plate **205** are configured to deliver the first gas A from the plenum **232** and into the first gas openings **211** of the showerhead **206**.

[0035] FIG. **2**C is an enlarged partial illustration of the showerhead **206** illustrated in FIG. **2**B, according to one implementation of the present disclosure. The showerhead **206** includes one or more bosses **240** that protrude from a first surface **236** of the showerhead **206**. The first gas openings **211** extend from a boss surface **237** to a second surface **238** of the showerhead **206**. The second surface **238** faces the processing volume **105** and is exposed thereto. The boss surfaces **237** of the bosses **240** contact the second surface **235** of the second plate **205**. In one example, one or more of the first gas openings **233** of the second plate **205** is aligned with one or more of the first gas openings **211** of the showerhead **206**.

[0036] As illustrated in FIGS. **2**B and **2**C, the first gas channel **221** of the gas manifold **201** is fluidly connected to the showerhead **206** and the processing volume **105**. The lid assembly **210** delivers the first gas A from a first gas source and into the processing volume **105**.

[0037] FIG. **2**D is an enlarged partial illustration of the lid assembly **210** illustrated in FIG. **2**A, according to one implementation of the present disclosure. The gas manifold **201** is configured to receive the second gas B through a second gas channel **241**. The second gas channel **241** is separate and distinct from the first gas channel **221** illustrated in FIG. **2**B. The second gas channel **241** is configured to deliver the second gas B to a second gas channel **242** of the isolator manifold **202**. The second gas channel **242** is separate and distinct from the first gas channel **222** of the isolator manifold **202**. The second gas channel **242** is configured to deliver the second gas B from the second gas channel **241** of the gas manifold **201** and into a second gas opening **243** of the gas box **203**. The second gas opening **243** is configured to deliver the second gas B into a second gas channel **244** of the gas box **203**. The second gas opening **243** is disposed radially outward of the first gas opening **223** of the gas box **203**.

[0038] The second gas channel **244** off the gas box **203** is separate and distinct from the first gas channel **25** illustrated in FIG. **2**B. The second gas channel **244** includes one or more second gas openings **246**. The second gas openings **246** of the second gas channel **244** are disposed radially outside of the first gas openings **226** of the first gas channel **225**. The second gas openings **246** are configured to deliver the second gas B from the second gas channel **244** and into a second gas opening **247** of the first plate **204**. The second gas opening **247** is disposed radially outside of the first gas openings **229** illustrated in FIG. **2**B. In one example, the second gas opening **247** is aligned with the second gas opening **246** of the second gas channel **244**.

[0039] The second gas opening **247** of the first plate **204** is configured to deliver the second gas B from the gas box **203** and into a second gas opening **248** of the second plate **205**. In one example, the second gas opening **247** of the first plate **204** is aligned with the second gas opening **248** of the second plate **205**.

[0040] FIG. **2**E is a partially-enlarged illustration of the showerhead **206** illustrated in FIG. **2**D, according to one implementation of the present disclosure. The second gas opening **248** of the second plate **205** is configured to deliver the second gas B from the second plate **205** and to a second gas channel **249** of the showerhead **206**. The second gas opening **248** is disposed radially outside of the first gas openings **233** of the second plate **205**. The second gas channel **249** is disposed radially outside of the bosses **240** and the first surface **236**. A wall **250** is disposed between the first surface **236** and the second gas channel **249**. The wall **250** includes one or more wall openings **251** that are configured to deliver the second gas B from the second gas channel **249** and into one or more gaps **252** that are disposed around and between the bosses **240**. The second gas openings **213** of the showerhead **206** extend from the first surface **236** to the second surface **238**. The second gas openings **213** are configured to deliver the second gas B from the gaps **252** and into the processing volume **105**.

[0041] As illustrated in FIGS. **2**D and **2**E, the second gas channel **241** of the gas manifold **201** is fluidly connected to the showerhead **206** and the processing volume **105**. The lid assembly **210** delivers the second gas B from a second gas source and into the processing volume **105**. The lid assembly **210** keeps the flow of the first gas A separate from the flow of the second gas B until first gas A and first gas B are introduced into the processing volume **105**. As an example, the boss surfaces **237** of the bosses **240** contact the second surface **235** and seal thereagainst. The bosses **240** thus fluidly separate the first gas A flowing through the first gas openings **211** from the second gas B flowing through the gaps **252** and the second gas openings **213**.

[0042] By keeping first gas A separate from second gas B, the lid assembly **210** facilitates mixing first gas A and second gas B in the processing volume **105** near the substrate **101** (illustrated in FIG. **1**). Mixing the first gas A and second gas B in the processing volume **105** facilitates reliable and efficient deposition of films onto the substrate **101**. The first gas A and second gas B do not mix prior to entering the processing volume **105**, mitigating or eliminating the effects of one or first gas A or second gas B breaking down relative to the other of first gas A or second gas B. For example, reducing the amount of a reactant gas that is broken down ensures that the reactant gas reaches the processing volume **105** at a density that facilitates mixing with another reactant gas to deposit a film onto a substrate.

[0043] FIG. **2**F is a partially-enlarged illustration of the lid assembly **210** illustrated in FIG. **2**A, according to one implementation of the present disclosure. The gas manifold **201** is configured to receive a third gas C into a third gas channel **253**. The third gas channel **253** is separate and distinct from the first gas channel **221** and the second gas channel **241**. The gas manifold **201** receives the third gas C from a third gas source. The third gas C is a cleaning gas, which may be activated by a remote plasma source (RPS) prior to introduction to the third gas channel **253**. In one example, the third gas C includes one or more carrier and/or cleaning gases such as argon, nitrogen trifluoride, and/or oxygen.

[0044] The third gas C can also be received by the gas manifold **201** into the central opening **215** from a third gas

source that is above the central opening **215**. In one example, the third gas C that is received by the third gas channel **253** bypasses an RPS and is not activated by the RPS, and the third gas C received by the central opening **215** passes through and is activated by the RPS.

[0045] The third gas channel **253** is configured to deliver the third gas C into the central opening **215** of the gas manifold **201**, the central opening **216** of the isolator manifold **202**, and the central opening **217** of the gas box **203**. The gas box **203** is configured to deliver the third gas C from the central opening **217** and into a third gas channel **254** of the gas box **203**. The lid assembly **210** is hence configured such that the third gas C bypasses the isolator manifold **202**, the first gas opening **223** of the gas box **203**, and the second gas opening **243** of the gas box **203**. These configurations allow for a simple design of the gas box **203** and for large flow rates of third gas C to flow through the central opening **215** of the gas manifold **201**.

[0046] The third gas channel **254** of the gas box **203** is separate and distinct from the first gas channel **225** and the second gas channel **244**. The third gas channel **254** includes one or more first openings **255** that are configured to deliver the third gas C from the second gas channel **244** and into the plenum **227** between the gas box **203** and the first plate **204**.

[0047] The third gas channel **254** includes one or more second openings **256** that are disposed radially outside of the first openings **255**. The second openings **256** are configured to deliver the third gas C from the third gas channel **254** and into a third gas opening **262** of the first plate **204**. The third gas opening **262** is separate and distinct from the second gas opening **247** of the first plate **204**. In one example, the third gas opening **262** is aligned with one or more of the second openings **256** of the third gas channel **254**.

[0048] One or more purge gases may be flowed through the lid assembly **210** to prevent backflow of the first gas A, second gas B, and/or the third gas C. As an example, purge gas may be flowed to prevent fluid (such as first gas A) from flowing from the plenum **227** and into the third gas channel **254**. As another example, purge gas may be flowed to prevent fluid (such as second gas B) from flowing from the second gas channel **249** and into the third gas openings **263**. The present disclosure also contemplates that the lid assembly **210** may include one or more valves to prevent backflow. As an example, one or more of each of the first openings **255**, first gas openings **226**, second gas openings **246**, third gas openings **263**, and/or third gas openings **262** may include valves. In one example, the valves include check valves or some other valve.

[0049] The first plate **204** is configured to deliver the third gas C from the plenum **227** and into one or more first gas openings **229**. The first gas openings **229** are configured to deliver the third gas C from the plenum **227** and into the plenum **232** between the first plate **204** and the second plate **205**. One or more first gas openings **233** of the second plate **205** are configured to deliver the third gas C from the plenum **232** and into the first gas openings **211** of the showerhead **206**. The first gas openings **211** are configured to introduce the third gas C into the processing volume **105**.

[0050] The third gas opening **262** of the first plate **204** is configured to deliver the third gas C into a third gas opening **263** of the second plate **205**. The third gas opening **263** is separate and distinct from the second gas opening **248** of the second plate **205**. The third gas opening **263** is configured to deliver the third gas C into the second gas channel **249** of the showerhead **206**. In one example, the third gas opening **263** of the second plate **205** is aligned with the third gas opening **262** of the first plate **204**.

[0051] The showerhead **206** is configured to deliver the third gas C, from the second gas channel **249**, and through one or more wall openings **251** of the wall **250** and into the gaps **252** disposed between and around the bosses **240** of the showerhead **206**. The showerhead is configured to deliver the third gas C from the gaps **252** and into the processing volume **105** through the one or more second gas openings **213**.

[0052] Hence, the lid assembly **210** is configured to deliver the third gas C through flow paths that the first gas A and the second gas B flow through, respectively, in the first plate **204**, second plate **205**, and the showerhead **206**. In examples where the third gas C is a cleaning gas, the lid assembly **210** can effectively, efficiently, and simultaneously clean the fluid paths for first gas A and second gas B. The lid assembly **210** can keep the flow paths for first gas A and second gas B separate prior to mixing the first gas A and the second gas B in the processing volume **105**. The lid assembly **210** can also clean fluid paths for first gas A and second gas B simultaneously.

[0053] FIG. **2**G is a schematic top-view illustration of the gas manifold **201** illustrated in FIG. **2**A, according to one implementation of the present disclosure. The gas manifold **201** includes a shoulder **264** disposed adjacent to the central opening **215**. The shoulder **264** supports the insulator **214** illustrated in FIG. **2**A. The first gas channel **221**, second gas channel **241**, and third gas channel **253** are separate and distinct, and are disposed in a spaced-apart relation from each other in the gas manifold **201**. The first gas channel **221** runs from an outer surface **268** of the gas manifold **201** to a bottom surface **266** of the gas manifold **201**. The second gas channel **241** runs from the outer surface **268** of the gas manifold **201** to the bottom surface **266** of the gas manifold **201**. The third gas channel **253** runs from the outer surface **268** to the inner surface **218** of the gas manifold **201**.

[0054] FIG. **2**H is a schematic top-view illustration of the gas box **203** illustrated in FIG. **2**A, according to one implementation of the present disclosure. The gas box **203** includes first gas channels **225**, second gas channels **244**, and third gas channels **254** that are separate and distinct. The first gas channels **225**, second gas channels **244**, and third gas channels **254** are disposed at a spaced-apart relation from each other in an alternating arrangement. One or more of each of the first gas channels **225**, second gas channels **244**, and/or third gas channels **254** may be disposed in different vertical planes in the gas box **203**. In the implementation illustrated in FIG. **2**F, the third gas channel **254** is disposed vertically below the first gas channel **225** illustrated in FIG. **2**B and the second gas channel **244** illustrated in FIG. **2**D. The present disclosure also contemplates that one or more of each of the first gas channels **225**, second gas channels **244**, and/or third gas channels **254** may be disposed in the same vertical plane in the gas box **203**. In the implementation illustrated in FIG. **2**D, the second gas channel **244** is disposed in the same vertical plane as the first gas channel **225**.

[0055] The first gas channels **225** each include one or more first gas openings **226** arranged in a linear arrangement extending radially outward. The second gas channels **244** each include one or more second gas openings **246** that are disposed radially outside of the first gas openings **226** of the

first gas channels **225**. The third gas channels **254** each include one or more first openings **255** and one or more second openings **256** arranged in a linear arrangement extending radially outward. The second openings **256** are disposed radially outside of the first openings **255** and the first gas openings **226** of the first gas channels **225**.

[0056] The first gas opening **223** is disposed circumferentially about the central opening **217** of the gas box **203**, and radially outside of the central opening **217**. The first gas opening **223** includes one or more first gas ports **267** that are configured to deliver first gas A from the first gas opening **223** and into the first gas channels **225**.

[0057] The second gas opening **243** is disposed circumferentially about the first gas opening **223** of the gas box **203**, and radially outside of the first gas opening **223**. The second gas opening **243** includes one or more second gas ports **269** that are configured to deliver second gas B from the second gas opening **243** and into the second gas channels **244**.

[0058] The third gas channels **254** are open to the central opening **217** of the gas box **203**. The gas box **203** is configured to deliver the third gas C from the central opening **217** and into the third gas channels **254**.

[0059] FIG. **2**I is a schematic top-view illustration of the first plate **204** illustrated in FIG. **2**A, according to one implementation of the present disclosure. In one example, the first plate **204** is a blocker plate. The first gas openings **229** are disposed in a concentric circular pattern on the first plate **204**, as illustrated in FIG. **2**I. The first plate **204** includes second gas openings **247** and third gas openings **262** disposed circumferentially on the first plate **204** in an alternating arrangement. The second gas openings **247** and the third gas openings **262** are disposed radially outside of the first gas openings **229**. The second gas openings **247** are oblong in shape. The third gas openings **262** and the first gas openings **229** are circular in shape. Each of the second gas openings **247** corresponds to a second gas opening **246** of a second gas channel **244** of the gas box **203**. Each of the third gas openings **262** corresponds to a second opening **256** of a third gas channel **254** of the gas box **203**. The second gas openings **247** and third gas openings **262** are disposed in first bosses **298** and second bosses **299**, respectively. The first bosses **298** and second bosses **299** protrude from the first plate **204**. The first plate **204** includes an inner shoulder **297** and an outer shoulder **296**.

[0060] FIG. **2**J is a schematic top-view illustration of the second plate **205** and the showerhead **206** illustrated in FIG. **2**A, according to one implementation of the present disclosure. The second plate **205** is disposed within the inner shoulder **209** of the showerhead **206**. The first gas openings **233** are disposed in a hexagonal pattern on the second plate **205**, as illustrated in FIG. **2**J. Second gas openings **248** and third gas openings **263** are disposed circumferentially on the second plate **205** in an alternating arrangement. The second gas openings **248** and the third gas openings **263** are disposed radially outside of the first gas openings **233**. The second gas openings **248** are oblong in shape. The first gas openings **233** and the third gas openings **263** are circular in shape. The second gas openings **248** correspond to the second gas openings **247** of the first plate **204**. The third gas openings **263** correspond to the third gas openings **262** of the first plate **204**. The second gas openings **248** and the third gas openings **263** are disposed in first bosses **290** and second bosses **291**, respectively. The first bosses **290** and the second bosses **291** protrude from the second plate **205**.

[0061] The present disclosure contemplates that the ports, openings, and/or channels disclosed herein may be a variety of shapes, such as circular or oblong. The shapes of the ports, openings, and/or channels may be used to accommodate various flow rates of the first gas A, second gas B, and/or third gas C, and may be used to facilitate producing seals between components or features of lid assembly **210**. As an example, the second gas openings **247** of the first plate **204** are illustrated as oblong in shape in FIG. **2**I to accommodate various flow rates of second gas B. The oblong shape of second gas openings **247** may be used to increase the cross-sectional areas of second gas openings **247** to facilitate accommodation of increased flow rates of second gas B. The oblong shape of second gas openings **247** can facilitate accommodation of increased flow rates of second gas B without the first bosses **298** interfering with a seal between the outer shoulder **296** and the inner shoulder **297**. The oblong shape of the second gas openings **247** also facilitates producing a seal between one or more aspects of gas box **203** and one or more aspects of first plate **204**, such as to prevent second gas B from flowing into the plenum **227**.

[0062] The shapes and sizes of the openings, channels, and/or ports disclosed herein may be modified based on process requirements for the substrate **101**, substrate processing chamber **104**, first gas A, second gas B, and/or third gas C.

[0063] FIG. **2**K is a schematic top-view illustration of the showerhead **206** illustrated in FIG. **2**A, according to one implementation of the present disclosure. The showerhead **206** includes the second gas channel **249** disposed circumferentially around the first gas openings **211**, bosses **240**, and second gas openings **213**. The second gas openings **213** are disposed around and between the bosses **240**. The second gas openings **213** are separated from the second gas channel **249** by the wall **250**. Wall openings **251** allow the second gas B to flow from the second gas channel **249** to the second gas openings **213**.

[0064] In one example, the bosses **240** and the first gas openings **211** are disposed in a hexagonal arrangement on the showerhead **206**, as illustrated in FIG. **2**K.

[0065] FIG. **2**L is a partially-enlarged view of the showerhead **206** illustrated in FIG. **2**K. The bosses **240** are disposed at a density such that respective centers of the bosses **240** are disposed at a distance L from each other. In one example, the distance L is within a range of about 0.0 inches to about 0.7 inches, such as about 0.34 inches to about 0.63 inches, such as about 0.34 inches or about 0.63 inches.

[0066] Although the present disclosure illustrates openings, ports, and channels in various orientations and configurations, the present disclosure contemplates that other orientations and/or configurations are possible. For example, the present disclosure contemplates that the plates, showerhead, manifolds, gas box, openings, ports, and/or channels disclosed herein can involve various shapes, sizes, numbers of iterations, lengths, dimensions, vertical orientations, horizontal orientations, and/or angled orientations. As an example, the number of second gas openings **213** on the showerhead **206** can be varied. The second gas openings **213** can also be disposed at various angles or can vary in shape, length, and/or size.

[0067] The present disclosure also contemplates that the first gas A, second gas B, and third gas C may be flowed through the lid assembly **210** and/or into the processing

volume **105** at various specified temperatures, pressures, flow rates, and/or molecular weights.

[0068] Benefits of the present disclosure include keeping gases separate until they reach a processing volume; mixing reactant gases above a substrate; high density mixing of gases; simultaneously cleaning separate flow paths; reliable and efficient deposition of a material onto a substrate, and reducing or preventing heat buildup and/or radical buildup on a lid assembly.

[0069] Aspects of the present disclosure include a lid assembly that separates gases prior to introducing the gases into a processing volume; a gas manifold with a first gas channel, a second gas channel, and a third gas channel; a gas box; a showerhead with first gas openings, second gas openings, bosses, and gaps; and an insulator.

[0070] It is contemplated that one or more of these aspects disclosed herein may be combined. Moreover, it is contemplated that one or more of these aspects may include some or all of the aforementioned benefits.

[0071] While the foregoing is directed to embodiments of the present disclosure, other and further embodiments of the disclosure may be devised without departing from the basic scope thereof. The present disclosure also contemplates that one or more aspects of the embodiments described herein may be substituted in for one or more of the other aspects described. The scope of the disclosure is determined by the claims that follow.

What is claimed is:

1. A lid assembly, comprising:
a gas manifold, the gas manifold comprising:
a first gas channel configured to receive a first gas defining a first gas path;
a second gas channel configured to receive a second gas, defining a second gas path, the second gas path fluidly isolated from the first gas channel; and
a third gas channel configured to receive a third gas, the third gas channel defining a third gas path, the third gas path in fluid communication with the first gas channel and the second gas channel; and
a showerhead fluidly coupled to the gas manifold, the showerhead comprising:
one or more first gas openings that are configured to receive the first gas while fluidly isolating the first gas from the second gas, and
one or more second gas openings that are configured to receive the second gas while fluidly isolation the second gas from both the first gas and the third gas.

2. The lid assembly of claim **1**, wherein the one or more first gas openings are disposed in one or more bosses on the showerhead, and the one or more second gas openings are disposed around or between the one or more bosses.

3. The lid assembly of claim **1**, wherein the one or more first gas openings and the one or more second gas openings of the showerhead are fluidly coupled to the third gas channel.

4. The lid assembly of claim **1**, further comprising
a gas box comprising:
a central opening coupled to a gas box third gas channel, the central opening fluidly coupled to the third gas channel;
a first gas opening coupled to a gas box first gas channel, the first gas opening disposed about the central opening and fluidly coupled to the first gas channel;
a second gas opening coupled to a gas box second gas channel, the second gas opening disposed about first gas opening and fluidly coupled to the second gas channel.

5. The lid assembly of claim **4**, further comprising:
a first plate coupled to an upper surface of the showerhead, the first plate comprising:
a first plate plenum fluidly coupled to the gas box first gas channel and gas box third gas channel, defining a fourth gas path combining the first and third gas paths;
a first plate second gas opening fluidly coupled to the gas box second gas channel and fluidly isolated from the plenum, further defining the second gas path.

6. The lid assembly of claim **5**, further comprising:
a second plate coupled to the upper surface of the showerhead and in contact with the gas box, the second plate comprising:
a second plate plenum fluidly coupled to the first plate plenum, further defining the fourth gas path;
a second plate third gas opening fluidly coupled to the first plate second gas opening separate from the second plate plenum, further defining the second gas path.

7. The lid assembly of claim **6**, wherein the gas manifold comprises a plurality of the first gas channels, wherein the plurality of first gas channels are arranged in a radially-extended spoked configuration.

8. A lid assembly, comprising:
a showerhead, comprising:
a plurality of first openings formed in a central location of a first surface of the showerhead;
a plurality of second openings formed in the first surface of the showerhead radially outward of the plurality of first openings, the plurality of second openings fluidly isolated from the plurality of second openings within the showerhead; and
a plurality of third openings formed in the first surface of the showerhead radially outward of the plurality of first openings;
and
a second plate coupled to the first surface of the showerhead, the second plate comprising:
a plurality of first gas openings of the second plate fluidly coupled to the plurality of first openings formed in the showerhead; first ; and
a plurality of second gas opening of the second plate fluidly coupled to the plurality of second gas openings formed in the first surface of the showerhead, wherein the plurality of second gas openings of second plate are fluidly isolated from the plurality of first gas openings formed in the first surface of the showerhead.

9. The lid assembly of claim **8** further comprising:
a first plate coupled to the second plate and the showerhead, the first plate comprising:
a first gas opening formed in the first plate, the first gas opening fluidly coupled to a plenum formed in the second plate, the plenum fluidly coupled to the plurality of first gas openings formed in the second plate; and
a second gas opening formed in the first plate, the second gas opening fluidly coupled to the plurality of second gas openings formed in the second plate.

10. The lid assembly of claim **9**, further comprising:
a gas box coupled to the first plate, the gas box comprising:
a first gas channel of the gas box fluidly coupled to a plenum of the first plate, the plenum of the first plate fluidly coupled to plurality of first gas openings of the first plate;
a second gas channel of the gas box fluidly coupled to the first plate gas opening;
a gas box central opening fluidly isolated from the first gas channel of the gas box and the second gas channel of the gas box within the gas box.

11. The lid assembly of claim **10** wherein the gas box first gas channel is disposed radially outward of the gas box central opening, and the gas box second gas channel is disposed radially outward of the gas box first gas channel.

12. The lid assembly of claim **11**, wherein the gas box includes a plurality of the second gas channels of the box, and the plurality of the second gas channels of the gas box are arranged in a radially-extending spoked configuration.

13. The lid assembly of claim **12**, wherein the gas box includes a central opening formed therein.

14. The lid assembly of claim **13**, wherein a ceramic shield is disposed in contact with the central opening of the gas box.

15. The lid assembly of claim **14**, wherein the ceramic shield comprises aluminum nitride, and includes one or more openings formed in a sidewall thereof.

16. A method for delivering a plurality of gasses to a processing chamber, comprising:
introducing a first gas from a first gas source into a process chamber through a first gas path formed in a lid assembly of the processing chamber;
introducing a second gas from a second gas source into the processing chamber through a second gas path formed through the lid assembly of the processing chamber, the second gas path fluidly isolated from the first gas path; and
introducing a third gas from a third gas source into the processing chamber through a third gas path, the third gas path in fluid communication with and overlapping with the first gas path and the second gas path.

17. The method of claim **16**, wherein the first gas path includes a first channel formed through a manifold of the lid assembly, a first gas channel formed in a gas box of the lid assembly, one or more first gas openings formed in a first plate of the lid assembly, more first gas openings formed in a second plate of the lid assembly, and one or more first gas openings of a showerhead of the lid assembly.

18. The method of claim **16** wherein the second gas path includes a second channel formed through a manifold of the lid assembly, a second gas channel formed in a gas box of the lid assembly, one or more first gas openings formed in a first plate of the lid assembly, more second gas openings formed in a second plate of the lid assembly, and one or more second gas openings of a showerhead of the lid assembly.

19. The method of claim **17** wherein the third gas path overlaps with the first gas path and the second gas path in the showerhead

20. The method of claim **19** further comprising introducing a fourth gas from a fourth gas source to at least one of the first gas path, the second gas path, or the third gas path, to prevent backflow of one of the first gas, the second gas, and the third gas.

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